

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor: Mervyn John Rose

Confirmation No.: 7787

Application No.: 10/773,696

Patent No.: 7,592,191 B2

Filing Date: February 6, 2004

Patent Date: September 22, 2009

For: FIELD EMISSION BACKPLATE

Attorney Docket No.: 85170-5100

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 C.F.R. § 1.323

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

It is requested that a Certificate of Correction be issued in connection with the above-identified patent correcting the errors listed on the accompanying Form PTO-1050. The corrections requested are as follows.

Title Page, Item (56) **References Cited**, FOREIGN PATENT DOCUMENTS, change "WO EP 0 578 428 1/1994" to - - EP EP 0 578 428 1/1994 - -. This change is requested to correct a typographical error.

Column 12, line 6 (claim 34, line 3), change "composing:" to - - comprising: - -. Support for this change appears in application claim 65.

This request is being made pursuant to 37 C.F.R. § 1.323 to correct errors of a clerical or typographical nature and do not involve changes that would constitute new matter or require reexamination. A fee of \$100 is believed to be due for this request. Please charge the required fees to Winston & Strawn LLP Deposit Account No. 50-1814. Please issue a Certificate of Correction in due course.

Respectfully submitted,

9/30/09

Date



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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO. : 7,592,191 B2
APPLICATION NO. : 10/773,696
DATED: : September 22, 2009
INVENTOR(S) : Rose et al.

Page 1 of 1

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:

Item (56) **References Cited**, FOREIGN PATENT DOCUMENTS, change
"WO EP 0 578 428 1/1994" to - - EP EP 0 578 428 1/1994 - -.

Column 12:

Line 6 (claim 34, line 3), change "composing:" to - - comprising: - -

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a transparent window, wherein electrons from the tips are emitted into the wide band-gap light emitting material.

27. The field emission device of claim 26, wherein the wide band-gap light emitting material is a light emitting polymer.

28. The field emission device of claim 26, wherein the transparent window is a thin film transparent metal.

29. The field emission device of claim 26, wherein one surface of the light emitting material is disposed on the plurality of tips of the field emission backplate and the transparent window is disposed on another surface of the light emitting material.

30. The field emission device of claim 22, wherein the device is a display device.

31. The field emission device of claim 22, wherein the tips of the field emission backplate are of a density of at least 100 per square micron.

32. A method of forming a field emission backplate according to claim 14, the method comprising:

depositing a thin film of amorphous semiconductor based material upon a substrate;

locally laser crystallizing a plurality of areas of the thin film amorphous semiconductor based material by exposure to at least one pulse laser interference pattern; and

growing crystalline semiconductor based material upon each of the plurality of crystallized areas of thin film amorphous semiconductor based material.

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33. The method of claim 32, further comprising the steps of depositing the thin film of amorphous semiconductor based material by plasma enhanced chemical vapor deposition.

34. A method of crystallizing areas of thin film amorphous semiconductor based material for use in the field emission backplate of claim 14, the method comprising:

forming a laser interferometer by splitting and recombining a laser beam;

placing a thin film of amorphous semiconductor based material in the plane of the recombination of the laser beam;

locally crystallizing areas of the thin film of amorphous semiconductor based material by subjecting the thin film to at least one laser pulse wherein the crystallized areas generated in the thin film amorphous semiconductor based material correspond to the interference pattern of the laser.

35. The method of claim 34, wherein for a backplate of amorphous semiconductor based material, wherein the semiconductor based material is hydrogenated amorphous silicon, the laser operates at a wavelength of around 532 nm to maximize absorption.

36. The method of claim 34, wherein the laser is a Nd:YAG laser.

comprising:

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